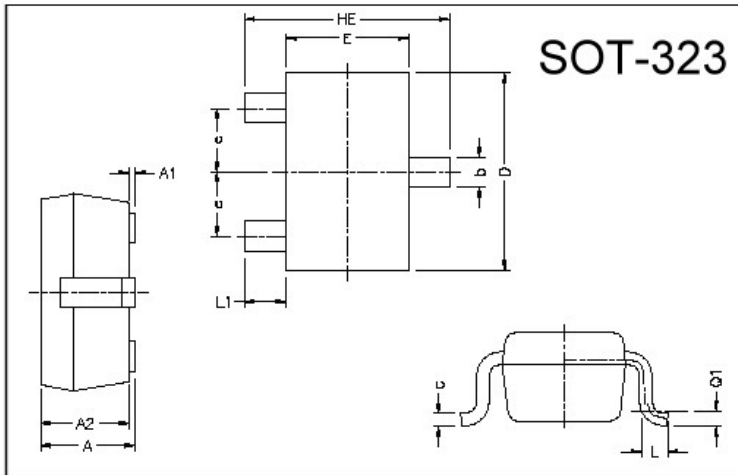
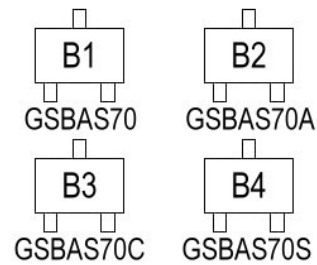
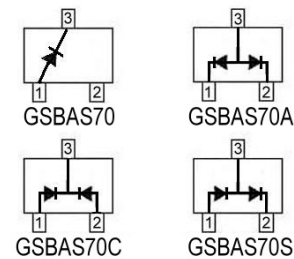


GSBAS70/A/C/S**SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 70V, CURRENT 70mA****Description**

These Schottky barrier diodes are designed for high speed switching applications, circuit protection and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Package Dimensions

| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 0.80 | 1.10 | L1 | 0.42 | REF. |
| A1 | 0 | 0.10 | L | 0.15 | 0.35 |
| A2 | 0.80 | 1.00 | b | 0.25 | 0.40 |
| D | 1.80 | 2.20 | c | 0.10 | 0.25 |
| E | 1.15 | 1.35 | e | 0.65 | REF. |
| HE | 1.80 | 2.40 | Q1 | 0.15 | BCS. |

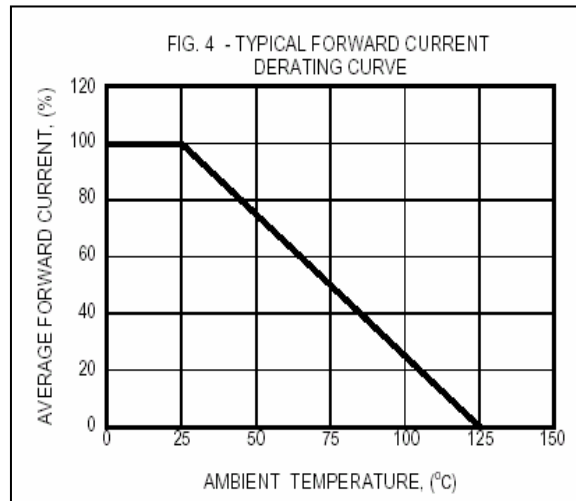
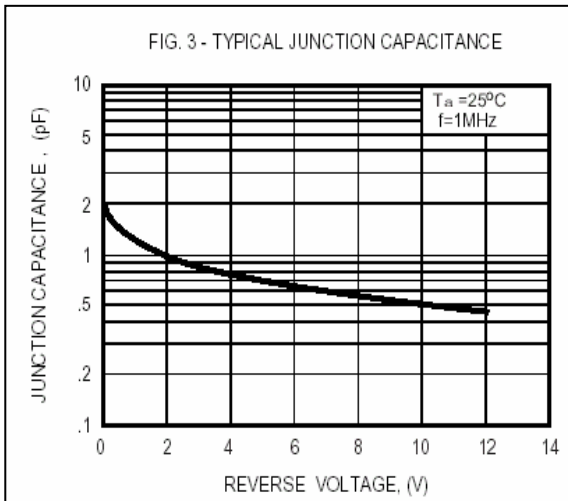
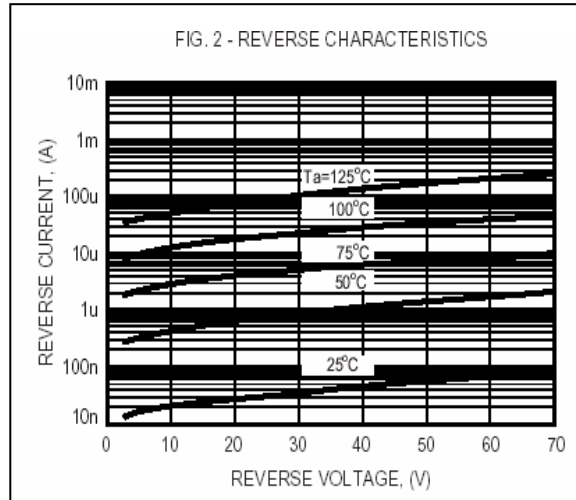
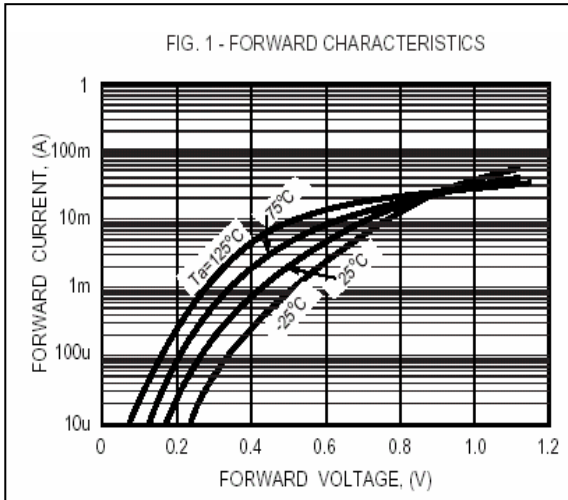
Marking :**Diagram :****Absolute Maximum Ratings at TA = 25°C**

| Parameter | Symbol | Ratings | Unit |
|--|------------------|------------|------|
| Operating Junction Temperature | T _j | +125 | °C |
| Storage Temperature | T _{stg} | -65 ~ +125 | °C |
| Maximum Repetitive Peak Reverse Voltage | V _{RRM} | 70 | V |
| Maximum Average Forward Rectified Current | I _o | 70 | mA |
| Non- Repetitive Peak Forward Surge Current @ t _p ≤ 1.0s | I _{FSM} | 100 | mA |
| Thermal Resistance Junction to Ambient Air | R _{θJA} | 445 | °C/W |
| Total Power Dissipation | PD | 225 | mW |

Electrical Characteristics (at TA = 25°C unless otherwise noted)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---------------------------|--------------------|------|------|------|------|--|
| Reverse Breakdown Voltage | V _{(BR)R} | 70 | - | - | V | I _R =10μA |
| Forward Voltage | V _F | - | - | 410 | mV | I _F =1mA |
| | | - | - | 750 | | I _F =10mA |
| | | - | - | 1000 | | I _F =15mA |
| Reverse Leakage Current | I _R | - | - | 100 | nA | V _R =50V |
| | | - | - | 10 | uA | V _R =70V |
| Total Capacitance | C _T | - | - | 2.0 | pF | V _R =0V, f=1MHz |
| Reverse Recover Time | T _{rr} | - | - | 5.0 | ns | I _F =I _R =10mA, R _L =100Ω, I _{rr} =1mA |

Characteristics Curve



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